## IS93C56A IS93C66A



# 2K-BIT/4K-BIT SERIAL ELECTRICALLY ERASABLE PROM

**AUGUST 2007** 

#### **FEATURES**

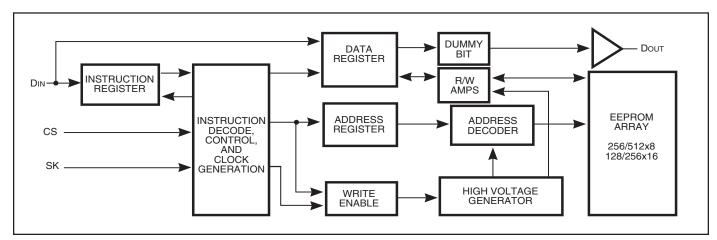
- Industry-standard Microwire Interface
  - Non-volatile data storage
  - Wide voltage operation: Vcc = 1.8V to 5.5V
  - V CC = 1.0 V to 3.5 V
  - Auto increment for efficient data dump
- · User Configured Memory Organization
  - By 16-bit or by 8-bit
- Hardware and software write protection
  - Defaults to write-disabled state at power-up
  - Software instructions for write-enable/disable
- Enhanced low voltage CMOS E<sup>2</sup>PROM technology
- · Versatile, easy-to-use Interface
  - Self-timed programming cycle
  - Automatic erase-before-write
  - Programming status indicator
  - Word and chip erasable
  - Chip select enables power savings
- Durable and reliable
  - 40-year data retention after 1M write cycles
  - 1 million write cycles
  - Unlimited read cycles
  - Schmitt-trigger inputs
- Industrial and Automotive Temperature Grade
- Lead-free available

#### **DESCRIPTION**

The IS93C56A/66A are 2kb/4kb non-volatile, ISSI <sup>®</sup> serial EEPROMs. They are fabricated using an enhanced CMOS design and process. The IS93C56A/66A contain power-efficient read/write memory, and organization of either 256/512 bytes of 8 bits or 128/256 words of 16 bits. When the ORG pin is connected to Vcc or left unconnected, x16 is selected; when it is connected to ground, x8 is selected. The IS93C56A/66A are fully backward compatible with IS93C56/66.

An instruction set defines the operation of the devices, including read, write, and mode-enable functions. To protect against inadvertent data modification, all erase and write instructions are accepted only while the devices are write-enabled. A selected x8 byte or x16 word can be modified with a single WRITE or ERASE instruction. Additionally, the two instructions WRITE ALL or ERASE ALL can program an entire array. Once a device begins its self-timed program procedure, the data out pin (Dout) can indicate the READY/ BUSY status by raising chip select (CS). The selftimed write cycle includes an automatic erasebefore-write capability. The devices can output any number of consecutive bytes/words using a single READ instruction.

#### **FUNCTIONAL BLOCK DIAGRAM**

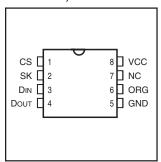


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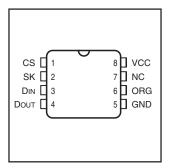


#### PIN CONFIGURATIONS

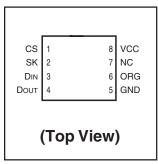
#### 8-Pin DIP, 8-Pin TSSOP



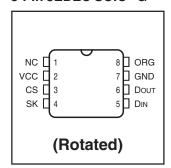
#### 8-Pin JEDEC SOIC "GR"



### 8-pad DFN



#### 8-Pin JEDEC SOIC "G"



#### PIN DESCRIPTIONS

CS	Chip Select
SK	Serial Data Clock
DIN	Serial Data Input
Dout	Serial Data Output
ORG	Organization Select
NC	Not Connected
Vcc	Power
GND	Ground

## **Applications**

The IS93C56A/66A are very popular in many applications which require low-power, low-density storage. Applications using these devices include industrial controls, networking, and numerous other consumer electronics.

#### **Endurance and Data Retention**

The IS93C56A/66A are designed for applications requiring up to 1M programming cycles (WRITE, WRALL, ERASE and ERAL). They provide 40 years of secure data retention without power after the execution of 1M programming cycles.

### **Device Operations**

The IS93C56A/66A are controlled by a set of instructions which are clocked-in serially on the Din pin. Before each low-to-high transition of the clock (SK), the CS pin must have already been raised to HIGH, and the Din value must be stable at either LOW or HIGH. Each

instruction begins with a start bit of the logical "1" or HIGH. Following this are the opcode (2 bits), address field (8 or 9 bits), and data, if appropriate. The clock signal may be held stable at any moment to suspend the device at its last state, allowing clock-speed flexibility. Upon completion of bus communication, CS would be pulled LOW. The device then would enter Standby mode if no internal programming is underway.

## Read (READ)

The READ instruction is the only instruction that outputs serial data on the Dout pin. After the read instruction and address have been decoded, data is transferred from the selected memory register into a serial shift register. (Please note that one logical "0" bit precedes the actual 8 or 16-bit output data string.) The output on Dout changes during the low-to-high transitions of SK (see Figure 3).

## Low Voltage Read

The IS93C56A/66A are designed to ensure that data read operations are reliable in low voltage environments. They provide accurate operation with Vcc as low as 1.8V.

## **Auto Increment Read Operations**

In the interest of memory transfer operation applications, the IS93C56A/66A are designed to output a continuous stream of memory content in response to a single read operation instruction. To utilize this function, the system asserts a read instruction specifying a start location address. Once the 8 or 16 bits of the addressed register have been clocked out, the data in consecutively higher address locations is output. The address will wrap around continuously with CS HIGH until the chip select (CS) control pin is brought LOW. This allows for single instruction data dumps to be executed with a minimum of firmware overhead.



## Write Enable (WEN)

The write enable (WEN) instruction must be executed before any device programming (WRITE, WRALL, ERASE, and ERAL) can be done. When Vcc is applied, this device powers up in the write disabled state. The device then remains in a write disabled state until a WEN instruction is executed. Thereafter, the device remains enabled until a WDS instruction is executed or until Vcc is removed. (See Figure 4.) (Note: Chip select must remain LOW until Vcc reaches its operational value.)

## Write (WRITE)

The WRITE instruction includes 8 or 16 bits of data to be written into the specified register. After the last data bit has been applied to DIN, and before the next rising edge of SK, CS must be brought LOW. If the device is write-enabled, then the falling edge of CS initiates the self-timed programming cycle (see WEN).

If CS is brought HIGH, after a minimum wait of 200 ns (5V operation) after the falling edge of CS (tcs) Dout will indicate the READY/BUSY status of the chip. Logical "0" means programming is still in progress; logical "1" means the selected register has been written, and the part is ready for another instruction (see Figure 5). The READY/BUSY status will not be available if: a) The CS input goes HIGH after the end of the self-timed programming cycle, twp; or b) Simultaneously CS is HIGH, Din is HIGH, and SK goes HIGH, which clears the status flag.

## Write All (WRALL)

The write all (WRALL) instruction programs all registers with the data pattern specified in the instruction. As with the WRITE instruction, the falling edge of CS must occur to initiate the self-timed programming cycle. If CS is then brought HIGH after a minimum wait of 200 ns (tcs), the Dout pin indicates the READY/BUSY status of the chip (see Figure 6). Vcc is required to be above 4.5V for WRALL to function properly.

## Write Disable (WDS)

The write disable (WDS) instruction disables all programming capabilities. This protects the entire device against accidental modification of data until a WEN instruction is executed. (When Vcc is applied, this part powers up in the write disabled state.) To protect data, a WDS instruction should be executed upon completion of each programming operation.

## **Erase Register (ERASE)**

After the erase instruction is entered, CS must be brought LOW. The falling edge of CS initiates the self-timed internal programming cycle. Bringing CS HIGH after a minimum of tcs, will cause Dout to indicate the READ/BUSY status of the chip: a logical "0" indicates programming is still in progress; a logical "1" indicates the erase cycle is complete and the part is ready for another instruction (see Figure 8).

#### Erase All (ERAL)

Full chip erase is provided for ease of programming. Erasing the entire chip involves setting all bits in the entire memory array to a logical "1" (see Figure 9). Vcc is required to be above 4.5V for ERALL to function properly.



## INSTRUCTION SET - IS93C56A (2kb)

				rganization	16-bit Org (ORG =	
Instruction <sup>(2)</sup>	Start Bit	OP Code	Address <sup>(1)</sup>	RG = GND) Input Data	Address <sup>(1)</sup>	Input Data
READ	1	10	x(A7-A0)	_	x(A6-A0)	_
WEN (Write Enable)	1	00	11xxxxxxxx	_	11xxxxxx	_
WRITE	1	01	x(A7-A0)	(D7-D0)	x(A6-A0)	(D15-D0)
WRALL (Write All Registers	s) 1	00	01xxxxxxx	(D7-D0)	01xxxxxx	(D15-D0)
WDS (Write Disable)	1	00	00xxxxxxx	_	00xxxxxx	_
ERASE	1	11	x(A7-A0)	_	x(A6-A0)	_
ERAL (Erase All Registers)	1	00	10xxxxxxx	_	10xxxxxx	_

#### Notes:

## INSTRUCTION SET - IS93C66A (4kb)

(0)			8-bit Organization (ORG = GND)		16-bit Organization (ORG = Vcc)		
Instruction <sup>(2)</sup>	Start Bit	OP Code	Address <sup>(1)</sup>	Input Data	Address <sup>(1)</sup>	Input Data	
READ	1	10	(A8-A0)	_	(A7-A0)	_	
WEN (Write Enable)	1	00	11xxxxxxx	_	11xxxxxx	_	
WRITE	1	01	(A8-A0)	(D7-D0)	(A7-A0)	(D15-D0)	
WRALL (Write All Register	rs) 1	00	01xxxxxxx	(D7-D0)	01xxxxxx	(D15-D0)	
WDS (Write Disable)	1	00	00xxxxxxx	_	00xxxxxx	_	
ERASE	1	11	(A8-A0)	_	(A7-A0)	_	
ERAL (Erase All Registers)	) 1	00	10xxxxxxx	_	10xxxxxx	_	

#### Notes:

<sup>1.</sup> x = Don't care bit.

<sup>2.</sup> If the number of bits clocked-in does not match the number corresponding to a selected command, all extra trailing bits are ignored, and WRITE, WRALL, ERASE, and ERAL are also ignored, but READ, WEN, WDS are accepted.

<sup>1.</sup> x = Don't care bit.

<sup>2.</sup> If the number of bits clocked-in does not match the number corresponding to a selected command, all extra trailing bits are ignored, and WRITE, WRALL, ERASE, and ERAL are also ignored, but READ, WEN, WDS are accepted.



### ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Parameter	Value	Unit
Vs	Supply Voltage	-0.5 to +6.5	V
VP	Voltage on Any Pin	-0.5 to Vcc + 0.5	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Тѕтс	Storage Temperature	-65 to +150	°C
Іоит	Output Current	5	mA

#### Notes:

### **OPERATING RANGE**

(IS93C56A-2, IS93C66A-2)

Range	Ambient Temperature	Vcc
Industrial	−40°C to +85°C	1.8V to 5.5V

Note: ISSI offers Industrial grade for Commercial applications (0°C to +70°C)

## **OPERATING RANGE**

(IS93C56A-3, IS93C66A-3)

Range	Ambient Temperature	Vcc
Automotive	-40°C to +125°C	2.5V to 5.5V

#### **CAPACITANCE**

Symbol	Parameter	Conditions	Max.	Unit
Cin	Input Capacitance	VIN = 0V	5	pF
Соит	Output Capacitance	Vout = 0V	5	pF

Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.



## DC ELECTRICAL CHARACTERISTICS

 $T_A = -40^{\circ}C$  to  $+85^{\circ}C$  for Industrial and  $-40^{\circ}C$  to  $+125^{\circ}C$  for Automotive.

Symbol	Parameter	Test Conditions	Vcc	Min.	Max.	Unit
V <sub>OL2</sub>	Output LOW Voltage	Ιοι = 100 μΑ	1.8V to 2.7V	_	0.2	V
V <sub>OL1</sub>	Output LOW Voltage	IoL = 2.1mA	2.7V to 5.5V	_	0.4	V
V <sub>OH2</sub>	Output HIGH Voltage	Ioн = -100 μA	1.8V to 2.7V	Vcc-0.2	_	V
V <sub>OH1</sub>	Output HIGH Voltage	Ioн = -400 μA	2.7V to 5.5V	2.4	_	V
VIH	Input HIGH Voltage		1.8V to 5.5V	0.7xVcc	Vcc+1	V
VIL	Input LOW Voltage		1.8V to 5.5V	-0.3	0.2xVcc	V
ILI	Input Leakage	VIN = 0V to Vcc (CS, SK,DIN,ORG)		0	2.5	μΑ
ILO	Output Leakage	Vout = 0V to Vcc, CS = 0V		0	2.5	μΑ

### Notes:

Automotive grade devices in this table are tested with Vcc = 2.5V to 5.5V. An operation with Vcc <2.5V is not specified.

## **POWER SUPPLY CHARACTERISTICS**

 $T_A = -40^{\circ}\text{C to} + 85^{\circ}\text{C for Industrial}, -40^{\circ}\text{C to} + 125^{\circ}\text{C for Automotive}.$ 

Syml	bol Parameter	Test Conditions	Vcc	Min.	Тур.	Max.	Unit	
lcc1	Vcc Read Supply Current	CS = V <sub>I</sub> H, SK = 1 MHz, CMOS input levels	1.8V	_	0.1	1	mA	
		CS = V <sub>IH</sub> , SK = 2 MHz, CMOS input levels	2.5V	_	0.2	1	mΑ	
		CS = VIH, SK = 2 MHz, CMOS input levels	5.0V	_	0.5	2	mA	
Icc2	Vcc Write Supply Current	CS = V <sub>I</sub> H, SK = 1 MHz, CMOS input levels	1.8V	_	0.5	1	mA	
		$CS = V_{IH}$ , $SK = 2$ MHz, CMOS input levels	2.5V	_	1	2	mΑ	
		CS = VIH, SK = 2 MHz, CMOS input levels	5.0V	_	2	3	mA	
IsB1	Standby Current	CS = GND, SK = GND,	1.8V	_	0.1	1	μΑ	
		ORG = Vcc or Floating (x16)	2.5V	_	0.1	2	μΑ	
			5.0V	_	0.2	4	μΑ	
IsB2	Standby Current	CS = GND, SK = GND,	1.8V	_	6	10	μΑ	
		ORG = GND (x8)	2.5V	_	6	10	μΑ	
			5.0V	_	10	15	μΑ	



## **AC ELECTRICAL CHARACTERISTICS**

 $TA = -40^{\circ}C$  to  $+85^{\circ}C$  for Industrial

Symbol	Parameter	<b>Test Conditions</b>		Min.	Max.	Unit
<b>f</b> sk	SK Clock Frequency		1.8V ≤ Vcc < 2.5V	0	1	Mhz
			$2.5V \leq Vcc < 4.5V$	0	2	Mhz
			$4.5V \leq Vcc \leq 5.5V$	0	3	Mhz
<b>t</b> skH	SK HIGH Time		1.8V ≤ Vcc < 2.5V	250	_	ns
			$2.5V \leq Vcc < 4.5V$	200	_	ns
			$4.5V \le Vcc \le 5.5V$	200	_	ns
tsĸL	SK LOW Time		$1.8V \le Vcc < 2.5V$	250	_	ns
			$2.5V \leq Vcc < 4.5V$	200	_	ns
			$4.5V \le Vcc \le 5.5V$	100	_	ns
tcs	Minimum CS LOW Time		1.8V ≤ Vcc < 2.5V	250	_	ns
			$2.5V \leq Vcc < 4.5V$	200	_	ns
			$4.5V \leq Vcc \leq 5.5V$	200	_	ns
tcss	CS Setup Time	Relative to SK	1.8V ≤ Vcc < 2.5V	200	_	ns
	·		$2.5V \leq Vcc < 4.5V$	100	_	ns
			$4.5V \le Vcc \le 5.5V$	50	_	ns
<b>t</b> DIS	Din Setup Time	Relative to SK	1.8V ≤ Vcc < 2.5V	100	_	ns
	·		$2.5V \leq Vcc < 4.5V$	50	_	ns
			$4.5V \leq Vcc \leq 5.5V$	50	_	ns
tсsн	CS Hold Time	Relative to SK	1.8V ≤ Vcc < 2.5V	0	_	ns
			$2.5V \leq Vcc < 4.5V$	0	_	ns
			$4.5V \le Vcc \le 5.5V$	0	_	ns
<b>t</b> DIH	Din Hold Time	Relative to SK	$1.8V \leq Vcc < 2.5V$	50	_	ns
			$2.5V \leq Vcc < 4.5V$	50	_	ns
			$4.5V \leq Vcc \leq 5.5V$	50	_	ns
<b>t</b> PD1	Output Delay to "1"	AC Test	$1.8V \le Vcc < 2.5V$	_	400	ns
			$2.5V \leq Vcc < 4.5V$		200	ns
			$4.5V \leq Vcc \leq 5.5V$	_	100	ns
t <sub>PD0</sub>	Output Delay to "0"	AC Test	$1.8V \le Vcc < 2.5V$	_	400	ns
			$2.5V \leq Vcc < 4.5V$	_	200	ns
			$4.5V \leq Vcc \leq 5.5V$	_	100	ns
tsv	CS to Status Valid	AC Test	1.8V ≤ Vcc < 2.5V	_	400	ns
			2.5V ≤ Vcc < 4.5V	_	200	ns
			$4.5V \leq Vcc \leq 5.5V$	_	200	ns
tof	CS to Dout in 3-state	AC Test, CS=VIL	1.8V ≤ Vcc < 2.5V		100	ns
		•	2.5V ≤ Vcc < 4.5V	_	100	ns
			$4.5V \le Vcc \le 5.5V$	_	100	ns
twp	Write Cycle Time		1.8V ≤ Vcc < 2.5V		10	ms
	•		$2.5V \leq Vcc < 4.5V$	_	5	ms
			$4.5V \le Vcc \le 5.5V$	_	5	ms

Notes:

1. C L = 100pF



## **AC ELECTRICAL CHARACTERISTICS**

 $TA = -40^{\circ}C$  to  $+125^{\circ}C$  for Automotive

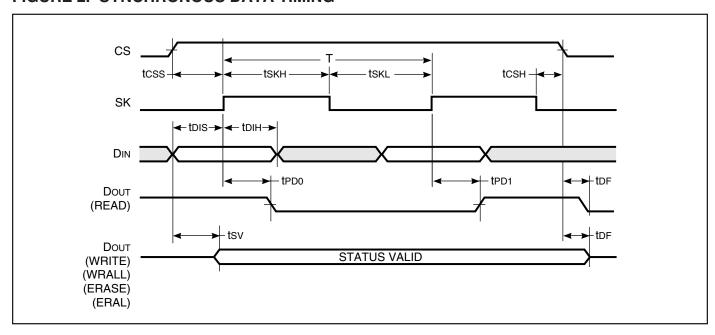
Symbol	Parameter	<b>Test Conditions</b>		Min.	Max.	Unit
fsк	SK Clock Frequency		2.5V ≤ Vcc < 4.5V	0	2	Mhz
			$4.5V \leq Vcc \leq 5.5V$	0	3	Mhz
<b>t</b> skH	SK HIGH Time		2.5V ≤ Vcc < 4.5V	200	_	ns
			$4.5V \leq Vcc \leq 5.5V$	200	_	ns
<b>t</b> skL	SK LOW Time		$2.5V \leq Vcc < 4.5V$	200	_	ns
			$4.5V \leq Vcc \leq 5.5V$	100	_	ns
tcs	Minimum CS LOW Time		2.5V ≤ Vcc < 4.5V	200	_	ns
			$4.5V \leq Vcc \leq 5.5V$	200	_	ns
tcss	CS Setup Time	Relative to SK	2.5V ≤ Vcc < 4.5V	100	_	ns
			$4.5V \leq Vcc \leq 5.5V$	50	_	ns
tois	Din Setup Time	Relative to SK	2.5V ≤ Vcc < 4.5V	50	_	ns
			$4.5V \leq Vcc \leq 5.5V$	50	_	ns
tсsн	CS Hold Time	Relative to SK	2.5V ≤ Vcc < 4.5V	0	_	ns
			$4.5V \leq Vcc \leq 5.5V$	0	_	ns
<b>t</b> DIH	Din Hold Time	Relative to SK	$2.5V \leq Vcc < 4.5V$	50	_	ns
			$4.5V \leq Vcc \leq 5.5V$	50	_	ns
<b>t</b> PD1	Output Delay to "1"	AC Test	$2.5V \leq Vcc < 4.5V$	_	200	ns
			$4.5V \leq Vcc \leq 5.5V$	_	100	ns
t <sub>PD0</sub>	Output Delay to "0"	AC Test	2.5V ≤ Vcc < 4.5V	_	200	ns
			$4.5V \leq Vcc \leq 5.5V$	_	100	ns
tsv	CS to Status Valid	AC Test	2.5V ≤ Vcc < 4.5V	_	200	ns
			$4.5V \leq Vcc \leq 5.5V$	_	200	ns
<b>t</b> DF	CS to Dout in 3-state	AC Test, CS=VIL	2.5V ≤ Vcc < 4.5V	_	100	ns
			$4.5V \leq Vcc \leq 5.5V$	_	100	ns
twp	Write Cycle Time		2.5V ≤ Vcc < 4.5V	_	5	ms
			$4.5V \leq Vcc \leq 5.5V$	_	5	ms

### Notes:

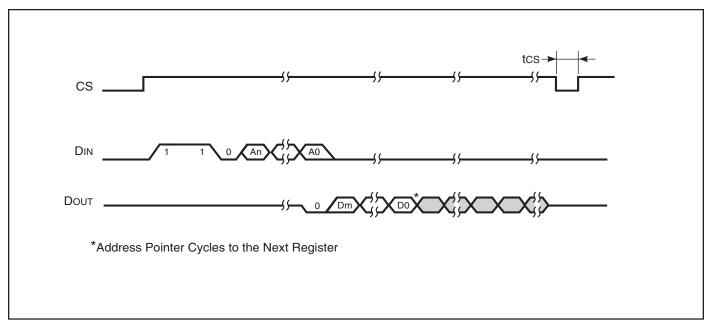
1. C L = 100pF



## FIGURE 2. SYNCHRONOUS DATA TIMING



## FIGURE 3. READ CYCLE TIMING

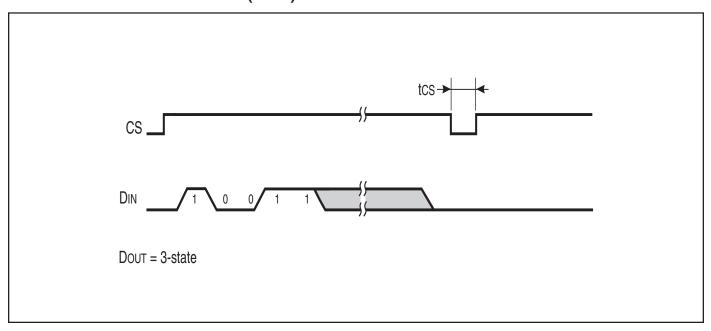


#### Notes:

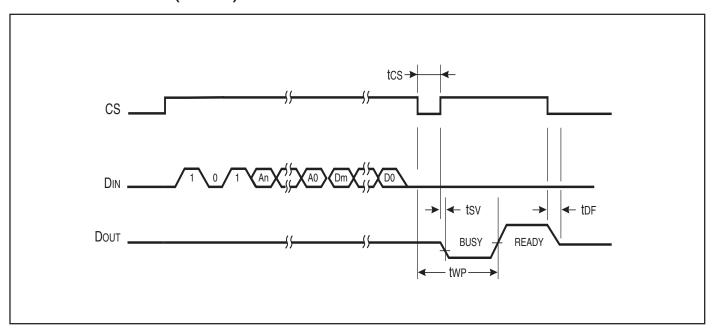
To determine address bits An-A0 and data bits Dm-Do, see Instruction Set for the specific device.



## FIGURE 4. WRITE ENABLE (WEN) CYCLE TIMING



## FIGURE 5. WRITE (WRITE) CYCLE TIMING

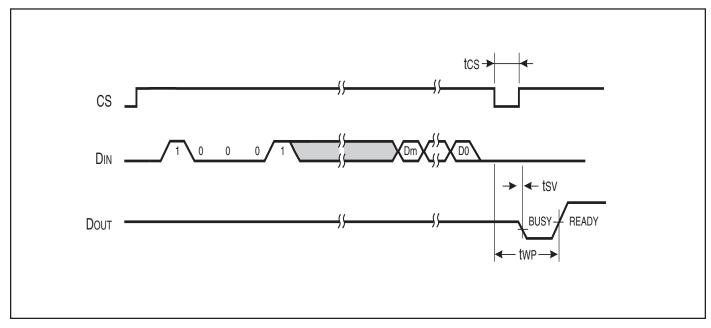


#### **Notes**

- 1. After the completion of the instruction (Dout is in READY status) then it may perform another instruction. If device is in **BUSY** status (Dout indicates **BUSY** status) then attempting to perform another instruction could cause device malfunction.
- 2. To determine address bits An-Ao and data bits Dm-Do, see Instruction Set for the specific device.



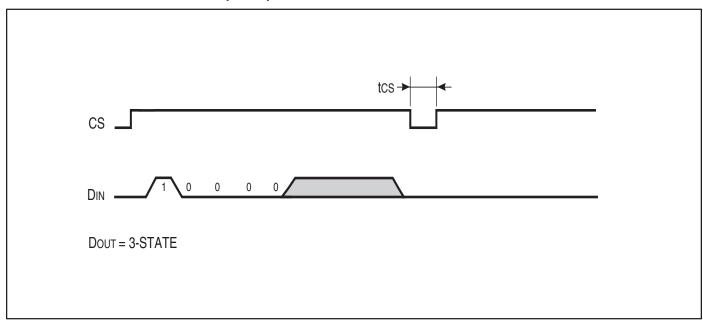
## FIGURE 6. WRITE ALL (WRALL) CYCLE TIMING



#### Notes:

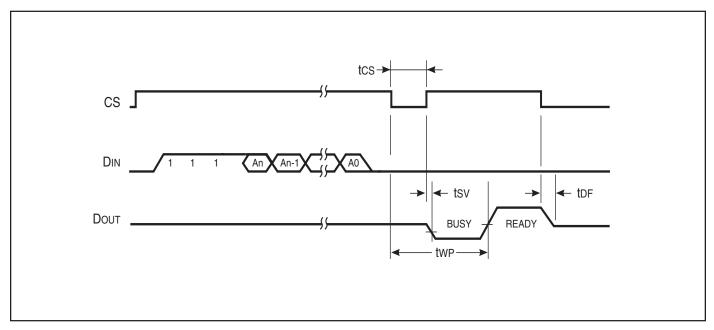
- 1. After the completion of the instruction (Dout is in READY status) then it may perform another instruction. If device is in **BUSY** status (Dout indicates **BUSY** status) then attempting to perform another instruction could cause device malfunction.
- 2. To determine data bits Dm-Do, see Instruction Set for the appropriate device.

## FIGURE 7. WRITE DISABLE (WDS) CYCLE TIMING





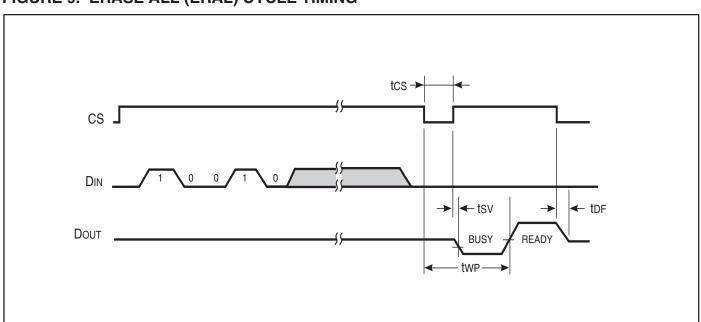
## FIGURE 8. ERASE (REGISTER ERASE) CYCLE TIMING



#### Notes:

To determine data bits An - A0, see Instruction Set for the appropriate device.

## FIGURE 9. ERASE ALL (ERAL) CYCLE TIMING



#### Note for Figures 8 and 9:

After the completion of the instruction (Dou $\tau$  is in READY status) then it may perform another instruction. If device is in  $\overline{\text{BUSY}}$  status (Dou $\tau$  indicates  $\overline{\text{BUSY}}$  status) then attempting to perform another instruction could cause device malfunction.



## **ORDERING INFORMATION**

Industrial Range: -40°C to +85°C

Voltage Range	Order Part No.	Package	
1.8V to 5.5V	IS93C56A-2PI	300-mil Plastic DIP	
	IS93C56A-2GRI	SOIC JEDEC	
	IS93C56A-2ZI	169-mil TSSOP	
1.8V to 5.5V	IS93C66A-2PI	300-mil Plastic DIP	
	IS93C66A-2GRI	SOIC JEDEC	
	IS93C66A-2ZI	169-mil TSSOP	

## Automotive Range: -40°C to +125°C, Lead-free

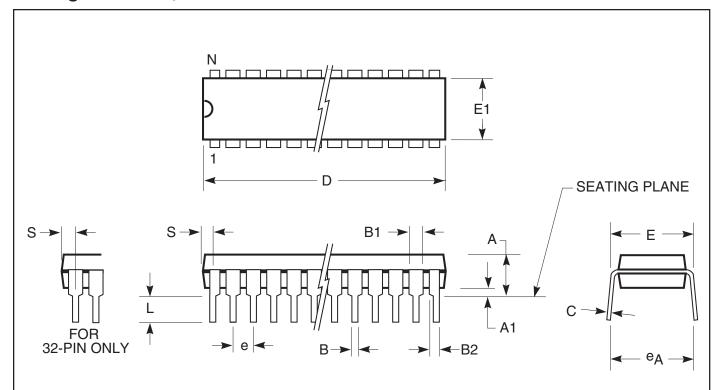
Voltage Range	Order Part No.	Package
2.5V to 5.5V	V to 5.5V IS93C56A-3PLA3 300-mil Plastic DIF	
	IS93C56A-3GRLA3	SOIC JEDEC
	IS93C56A-3ZLA3	169-mil TSSOP
2.5V to 5.5V	IS93C66A-3PLA3	300-mil Plastic DIP
	IS93C66A-3GRLA3	SOIC JEDEC
	IS93C66A-3ZLA3	169-mil TSSOP

## Industrial Range: -40°C to +85°C, Lead-free

Voltage Range	Order Part No.	Package
1.8V to 5.5V	IS93C56A-2PLI IS93C56A-2DLI IS93C56A-2GLI	300-mil Plastic DIP 8-pad DFN SOIC JEDEC
	IS93C56A-2GRLI IS93C56A-2ZLI	SOIC JEDEC 169-mil TSSOP
1.8V to 5.5V	IS93C66A-2PLI IS93C66A-2DLI	300-mil Plastic DIP 8-pad DFN
	IS93C66A-2GRLI IS93C66A-2ZLI	SOIC JEDEC 169-mil TSSOP



300-mil Plastic DIP Package Code: N,P



	MILLIMETERS		INCHES	
Sym.	Min.	Max.	Min.	Max.
N0. Leads		8		
Α	3.68	4.57	0.145	0.180
A1	0.38	_	0.015	_
В	0.36	0.56	0.014	0.022
B1	1.14	1.52	0.045	0.060
B2	0.81	1.17	0.032	0.046
С	0.20	0.33	0.008	0.013
D	9.12	9.53	0.359	0.375
E	7.62	8.26	0.300	0.325
E1	6.20	6.60	0.244	0.260
ед	8.13	9.65	0.320	0.380
е	2.54 BSC		0.100	) BSC
L	3.18		0.125	
S	0.64	0.762	0.025	0.030

#### Notes:

- 1. Controlling dimension: inches, unless otherwise specified.
- 2. BSC = Basic lead spacing between centers.
- Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.
- Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.

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300-mil Plastic DIP Package Code: N,P

	MILLIMETERS		INCHES		
Sym.	Min.	Max.	Min.	Max.	
N0. Leads	1	6			
Α	3.68	4.57	0.145	0.180	
A1	0.25	_	0.010	_	
В	0.46 BSC 0.018 BSC		BSC		
B1	1.52 BSC		0.060 BSC		
B2	_	_	_	_	
С	0.13	0.38	0.005	0.015	
D	18.92	19.18	0.745	0.755	
E	7.44	8.13	0.293	0.320	
E1	6.22	6.48	0.245	0.255	
e <sub>A</sub>	8.13	9.65	0.320	0.380	
e	2.54	BSC	0.100	BSC	
L	3.05	3.56	0.120	0.140	
S	0.38	0.89	0.015	0.035	

	MILL	IMETERS	INCHES			IMETERS INCHE	
Sym.	Min.	Max.	Min.	Max.			
N0. Leads		20					
A	3.68	4.57	0.145	0.180			
A1	0.38	_	0.015	_			
В	0.36	0.56	0.014	0.022			
B1	1.14	1.78	0.045	0.070			
B2	_	_	_	_			
С	0.20	0.36	0.008	0.014			
D	25.91	26.42	1.020	1.040			
E	7.49	8.26	0.295	0.325			
E1	6.01	7.11	0.240	0.280			
e <sub>A</sub>	_	10.92	_	0.430			
e	2.54 BSC		0.100	BSC			
L	3.05	3.81	0.120	0.150			
S	1.02	1.52	0.040	0.060			

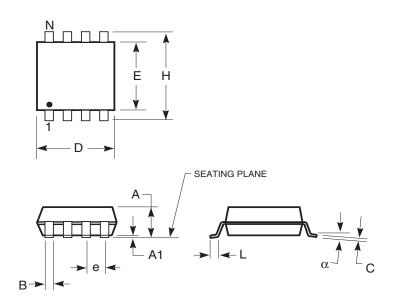
	MILLI	METERS	INC	HES
Sym.	Min.	Max.	Min.	Max.
N0. Leads		28		
A	3.68	4.57	0.145	0.180
A1	0.25	_	0.010	_
В	0.41	0.56	0.016	0.022
B1	1.27	1.78	0.050	0.070
B2	0.81	1.17	0.032	0.046
С	0.20	0.38	0.008	0.015
D	35.05	35.56	1.380	1.400
E	7.49	8.00	0.295	0.315
E1	6.99	7.49	0.275	0.295
e <sub>A</sub>	7.87	10.16	0.310	0.400
е	2.54 BSC		0.100	) BSC
L	3.05	3.81	0.120	0.150
S	0.51	1.06	0.020	0.042

	MILLIMETERS		INC	HES
Sym.	Min.	Max.	Min.	Max.
N0. Leads		32		
Α	3.56	4.57	0.140	0.180
A1	0.38	_	0.015	_
В	0.38	0.53	0.015	0.021
B1	1.02	1.78	0.040	0.070
B2	_	_	_	_
С	0.13	0.38	0.005	0.015
D	40.51	40.77	1.595	1.605
E	7.75	8.26	0.305	0.325
E1	7.24	7.22	0.285	0.292
ед	8.38	9.40	0.33	0.370
е	2.54 BSC		0.100	) BSC
L	3.05	3.81	0.120	0.150
S	1.65	2.16	0.065	0.085





150-mil Plastic SOP Package Code: G, GR



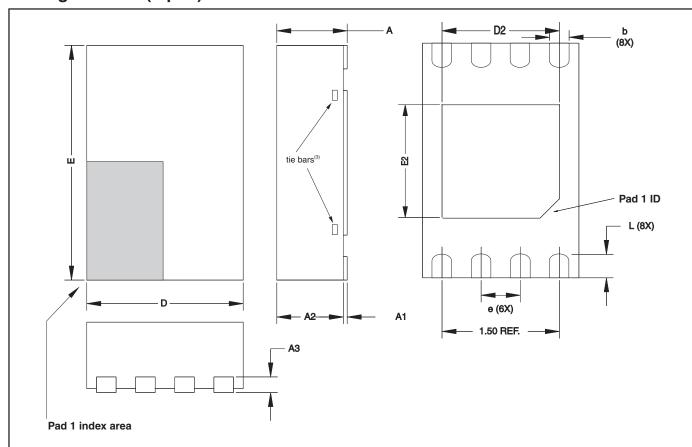
150-mil Plastic SOP (G, GR)						
Symbol	Min	Max	Min	Max		
Ref. Std.	Inc	hes	mm			
No. Leads		8	8			
A	_	0.068	_	1.73		
A1	0.004	0.009	0.1	0.23		
В	0.013	0.020	0.33	0.51		
С	0.007	0.010	0.18	0.25		
D	0.189	0.197	4.8	5		
Е	0.150	0.157	3.81	3.99		
Н	0.228	0.245	5.79	6.22		
е	0.050	BSC	1.27 BS	SC SC		
L	0.020	0.035	0.51	0.89		

#### Notes

- 1. Controlling dimension: inches, unless otherwise specified.
- 2. BSC = Basic lead spacing between centers.
- Dimensions D and E1 do not include mold flash protrusions and should be measured from the bottom of the package.
- 4. Formed leads shall be planar with respect to one another within 0.004 inches at the seating plane.



Dual Flat No-Lead Package Code: D (8-pad)



### **DFN**

#### **MILLIMETERS**

Sym.	Min.	Nom.	Max.	
N0.				
Pad		8		
D	2	.00 BS	С	
Е	3	.00 BS	С	
D2	1.50		1.75	
E2	1.60	_	1.90	
Α	0.70	0.75	0.80	
A1	0.0	0.02	0.05	
A2	_	_	0.75	
A3	C	.20 RE	F	
L	0.30	0.40	0.50	
е	0	.50 BS	С	
b	0.18	0.25	0.30	

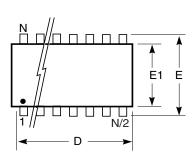
#### Notes:

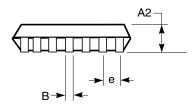
- 1. Refer to JEDEC Drawing MO-229.
- This is the metallized terminal and is measured between 0.18 mm and 0.30 mm from the terminal tip. The terminal may have a straight end instead of rounded.
- Package may have exposed tie bars, ending flush with package edge.

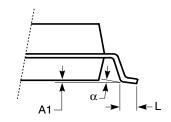
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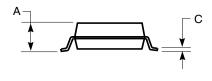


Thin Shrink Small Outline TSSOP Package Code: Z (8 pin, 14 pin)









TSSOP (Z)					
Ref. Std. JEDEC MO-153					
No. Leads	6	8			
	Millim	eters	Inch	nes	
Symbol	Min	Max	Min	Max	
A	_	1.20	_	0.047	
A1	0.05	0.15	0.002	0.006	
A2	0.80	1.05	0.032	0.041	
В	0.19	0.30	0.007	0.012	
С	0.09	0.20	0.004	0.008	
D	2.90	3.10	0.114	0.122	
E1	4.30	4.50	0.169	0.177	
Е	6.40	) BSC	0.25	2 BSC	
е	0.65	5 BSC	0.02	6 BSC	
L	0.45	0.75	0.018	0.030	
α	_	8°	_	8°	

TSSOP (Z)					
Ref. Std.		JEDEC	MO-153		_
No. Leads	3	1	4		
	Millim	eters	Inch	es	_
Symbol	Min	Max	Min	Max	_
A	_	1.20	_	0.047	_
A1	0.05	0.15	0.002	0.006	
A2	0.80	1.05	0.031	0.041	
В	0.19	0.30	0.007	0.012	
С	0.09	0.20	0.0035	0.008	
D	4.90	5.10	0.193	0.201	
E1	4.30	4.50	0.170	0.177	
Е	6.40	BSC	0.25	2 BSC	
е	0.65	BSC	0.02	6 BSC	_
L	0.45	0.75	0.0177	0.0295	
α	_	8°	_	8°	_

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